



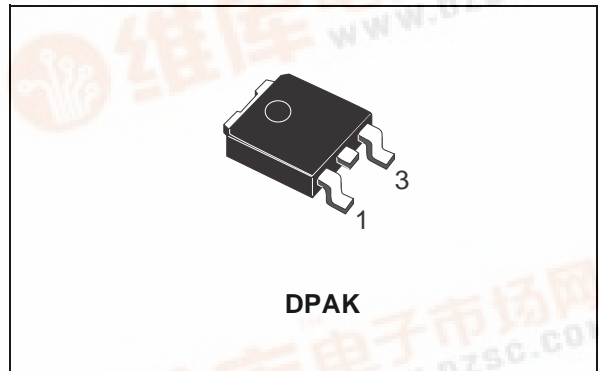
STGD7NB60H

N-CHANNEL 7A - 600V - DPAK

PowerMESH™ IGBT

TYPE	V _{CES}	V _{CE(sat)}	I _C
STD7NB60H	600 V	< 2.8 V	7 A

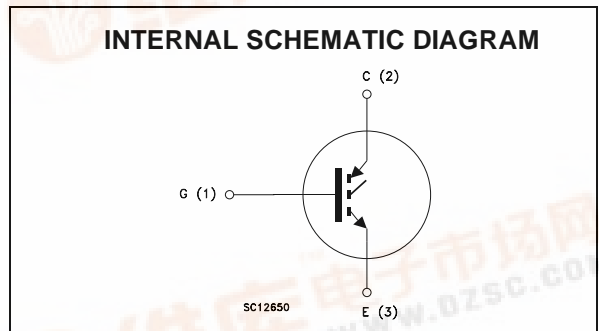
- HIGH INPUT IMPEDANCE
- LOW ON-VOLTAGE DROP (V_{CEsat})
- OFF LOSSES INCLUDE TAIL CURRENT
- LOW GATE CHARGE
- HIGH CURRENT CAPABILITY
- VERY HIGH FREQUENCY OPERATION
- CO-PACKAGED WITH TURBOSWITCHT
- TYPICAL SHORT CIRCUIT WITHSTAND TIME 5MICROS S-family, 4 micro H family
- ANTIPARALLEL DIODE



DESCRIPTION

Using the latest high voltage technology based on a patented strip layout, STMicroelectronics has designed an advanced family of IGBTs, the PowerMESH™ IGBTs, with outstanding performances.

The suffix "H" identifies a family optimized for high frequency applications (up to 50kHz) in order to achieve very high switching performances (reduced t_{fall}) maintaining a low voltage drop.



APPLICATIONS

- HIGH FREQUENCY MOTOR CONTROLS
- SMPS and PFC IN BOTH HARD SWITCH AND RESONANT TOPOLOGIES

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CES}	Collector-Emitter Voltage (V _{GS} = 0)	600	V
V _{ECR}	Emitter-Collector Voltage	20	V
V _{GE}	Gate-Emitter Voltage	± 20	V
I _C	Collector Current (continuous) at T _C = 25°C	14	A
I _C	Collector Current (continuous) at T _C = 100°C	7	A
I _{CM} (■)	Collector Current (pulsed)	56	A
P _{TOT}	Total Dissipation at T _C = 25°C	55	W
	Derating Factor	0.44	W/°C
T _{stg}	Storage Temperature	-65 to 150	°C
T _j	Max. Operating Junction Temperature	150	°C

STGD7NB60H

THERMAL DATA

Rthj-case	Thermal Resistance Junction-case Max	2.27	°C/W
Rthj-amb	Thermal Resistance Junction-ambient Max	100	°C/W
Rthc-sink	Thermal Resistance Case-sink Typ	1.5	°C/W

ELECTRICAL CHARACTERISTICS (TCASE = 25 °C UNLESS OTHERWISE SPECIFIED)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{BR(CES)}$	Collectro-Emitter Breakdown Voltage	$I_C = 250 \mu A, V_{GE} = 0$	600			V
I_{CES}	Collector cut-off ($V_{GE} = 0$)	$V_{CE} = \text{Max Rating}, T_C = 25 \text{ }^\circ\text{C}$ $V_{CE} = \text{Max Rating}, T_C = 125 \text{ }^\circ\text{C}$			10 100	μA μA
I_{GES}	Gate-Emitter Leakage Current ($V_{CE} = 0$)	$V_{GE} = \pm 20V, V_{CE} = 0$			± 100	nA

ON (1)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{GE(th)}$	Gate Threshold Voltage	$V_{CE} = V_{GE}, I_C = 250\mu A$	3		5	V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$V_{GE} = 15V, I_C = 7 A$ $V_{GE} = 15V, I_C = 7 A, T_j = 125^\circ\text{C}$		2.3 1.9	2.8	V V

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g_{fs}	Forward Transconductance	$V_{CE} = 25 V, I_C = 3 A$	3.5	5		S
C_{ies}	Input Capacitance	$V_{CE} = 25V, f = 1 \text{ MHz}, V_{GE} = 0$		560		pF
C_{oes}	Output Capacitance			68		pF
C_{res}	Reverse Transfer Capacitance				15	
Q_g Q_{ge} Q_{gc}	Total Gate Charge Gate-Emitter Charge Gate-Collector Charge	$V_{CE} = 480V, I_C = 7 A,$ $V_{GE} = 15V$		42 7.9 17.6	55	nC nC nC
I_{CL}	Latching Current	$V_{clamp} = 480 V, T_j = 150^\circ\text{C}$ $R_G = 10 \Omega$	28			A

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on Delay Time Rise Time	$V_{CC} = 480 V, I_C = 7 A$ $R_G = 10\Omega, V_{GE} = 15 V$		15 48		ns ns
$(di/dt)_{on}$ E_{on}	Turn-on Current Slope Turn-on Switching Losses	$V_{CC} = 480 V, I_C = 7 A, R_G = 10\Omega$ $V_{GE} = 15 V, T_j = 125^\circ\text{C}$		160 70		A/ μs μJ

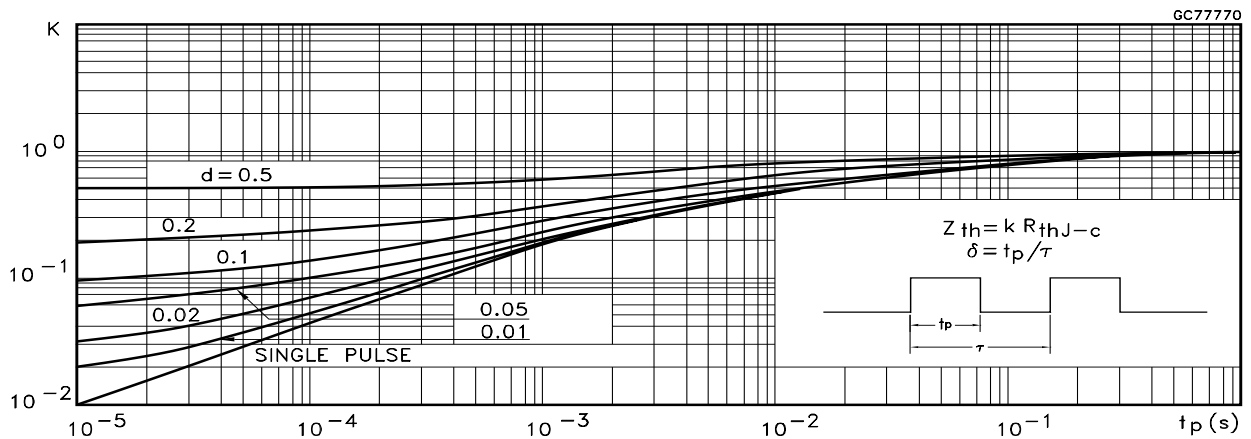
ELECTRICAL CHARACTERISTICS (CONTINUED)

SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit	
t_c	Cross-over Time	$V_{CC} = 480\text{ V}, I_C = 7\text{ A},$ $R_{GE} = 10\ \Omega, V_{GE} = 15\text{ V}$		85		ns	
$t_r(V_{off})$	Off Voltage Rise Time			20		ns	
$t_{d(off)}$	Delay Time			75		ns	
t_f	Fall Time			70		ns	
$E_{off(**)}$	Turn-off Switching Loss				85		μJ
E_{ts}	Total Switching Loss				130		μJ
t_c	Cross-over Time	$V_{CC} = 480\text{ V}, I_C = 3\text{ A},$ $R_{GE} = 10\ \Omega, V_{GE} = 15\text{ V}$ $T_j = 125\text{ }^\circ\text{C}$		150		ns	
$t_r(V_{off})$	Off Voltage Rise Time			50		ns	
$t_{d(off)}$	Delay Time			110		ns	
t_f	Fall Time			110		ns	
$E_{off(**)}$	Turn-off Switching Loss				220		μJ
E_{ts}	Total Switching Loss				290		μJ

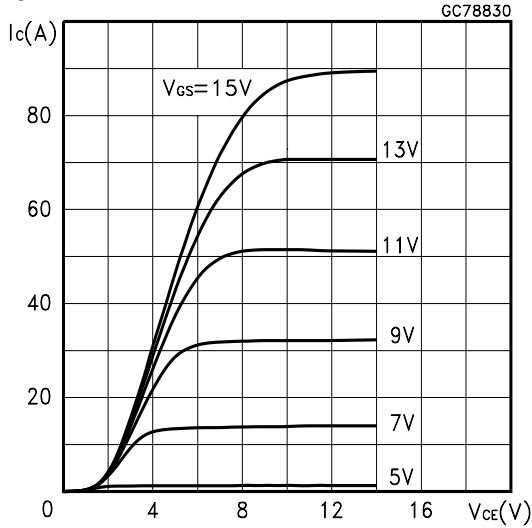
Note: 1. Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %.
 2. Pulse width limited by max. junction temperature.
 (**)Losses include Also the Tail (Jedec Standardization)

Thermal Impedance

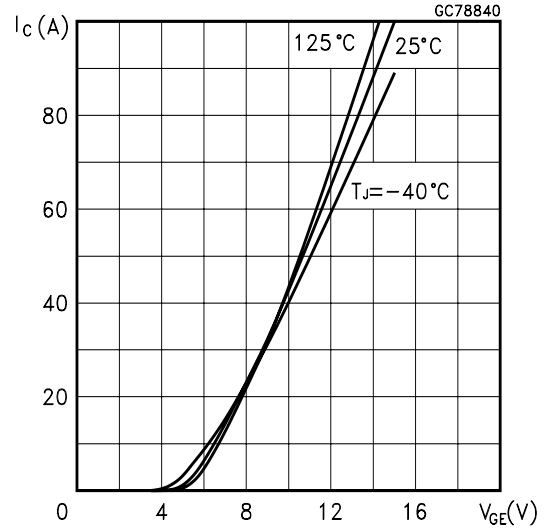


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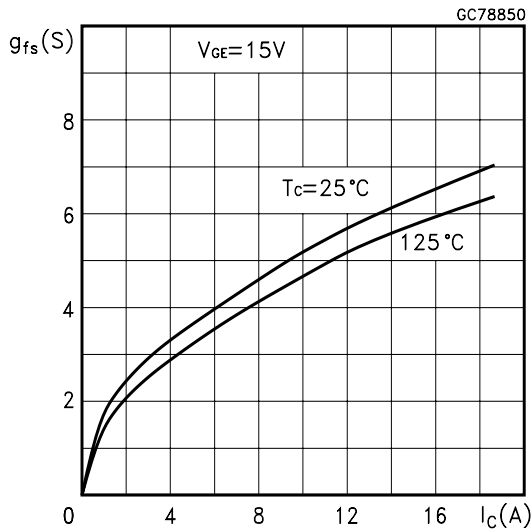
Output Characteristics



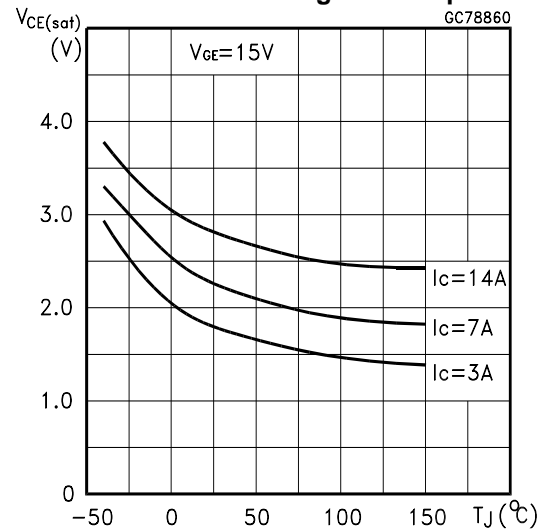
Transfer Characteristics



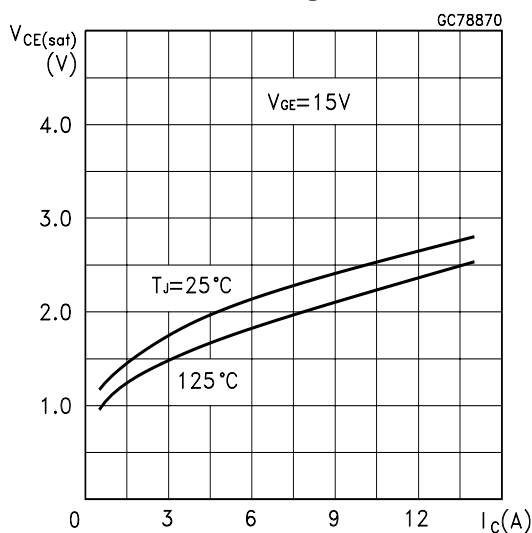
Transconductance



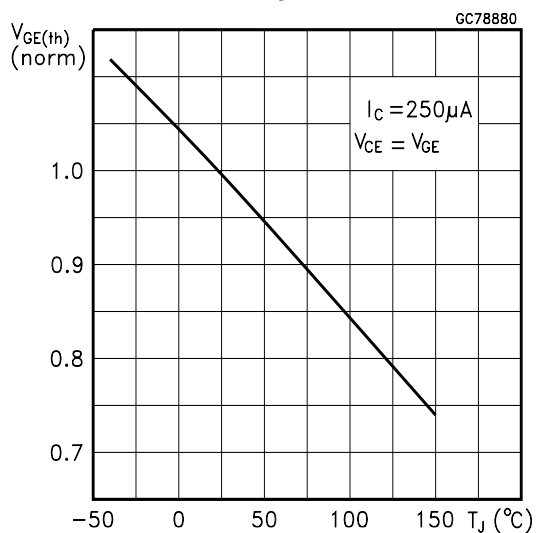
Collector-Emitter On Voltage vs Temperature



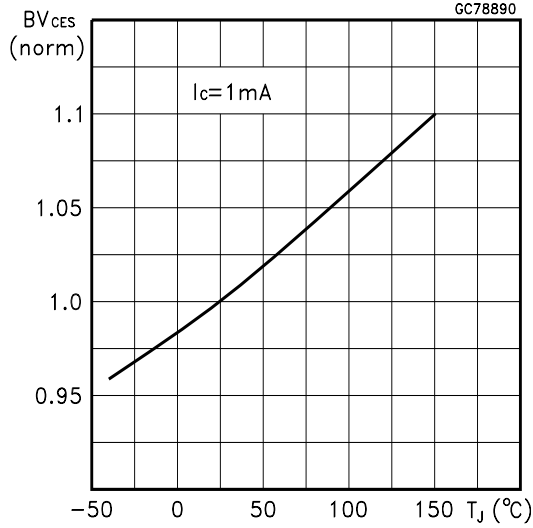
Collector-Emitter On Voltage vs Collector Current



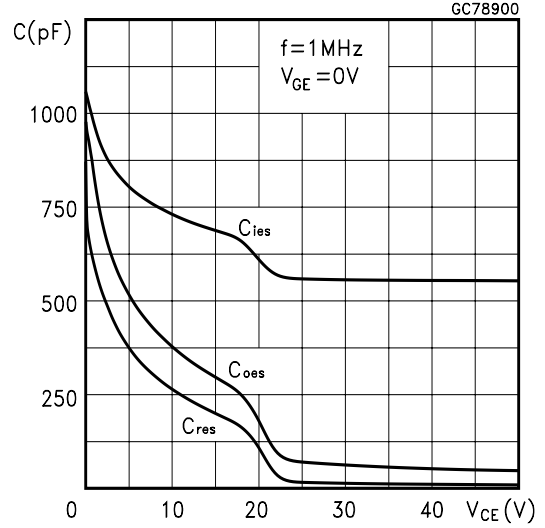
Gate Threshold vs Temperature



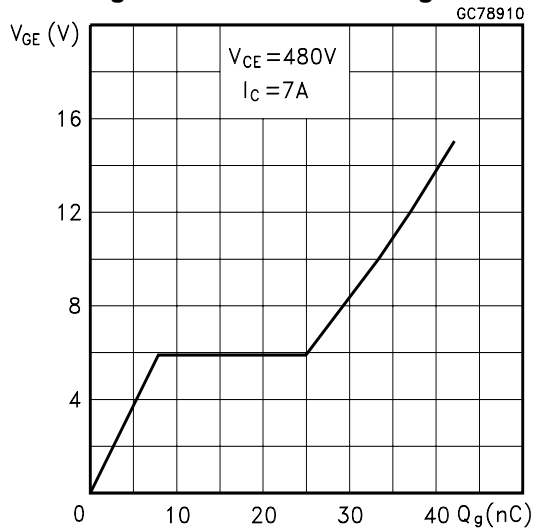
Normalized Breakdown Voltage vs Temperature



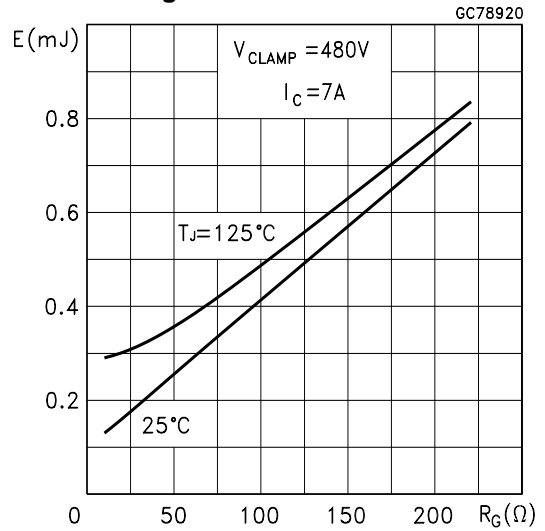
Capacitance Variations



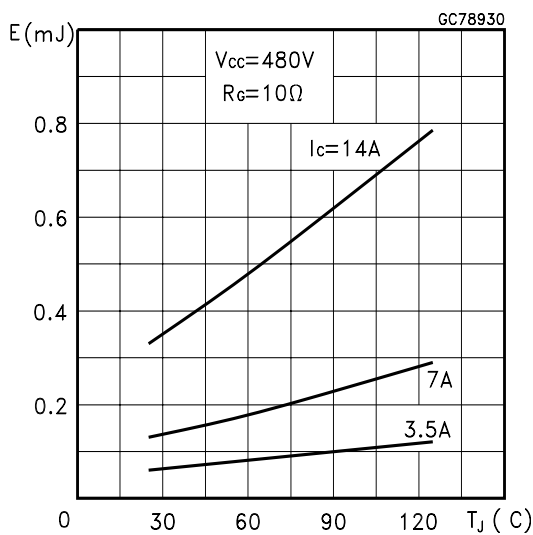
Gate Charge vs Gate-Emitter Voltage



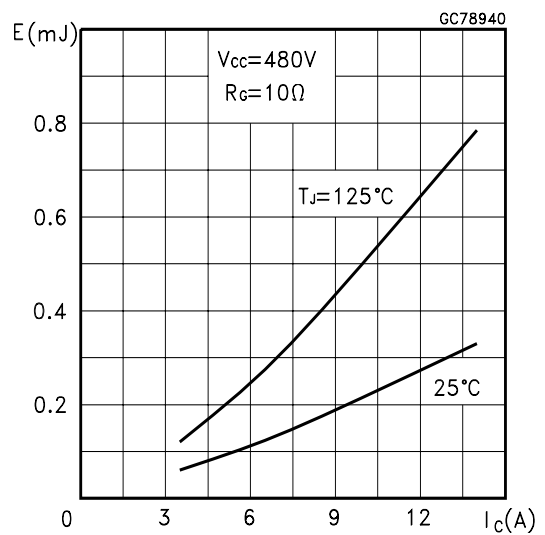
Total Switching Losses vs Gate Resistance



Total Switching Losses vs Temperature



Total Switching Losses vs Collector Current



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Switching Off Safe Operating Area

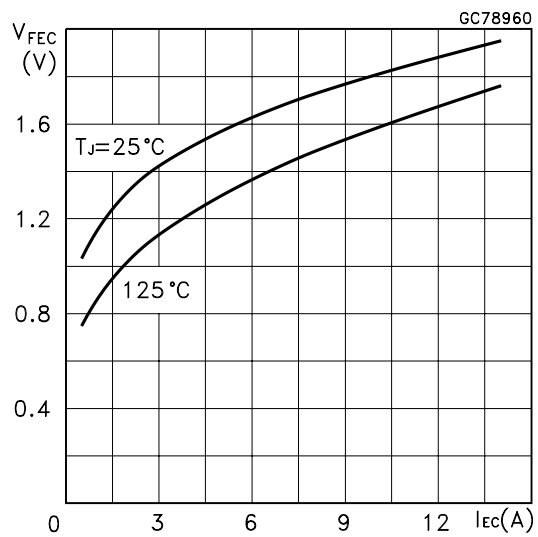


Fig. 1: Gate Charge test Circuit

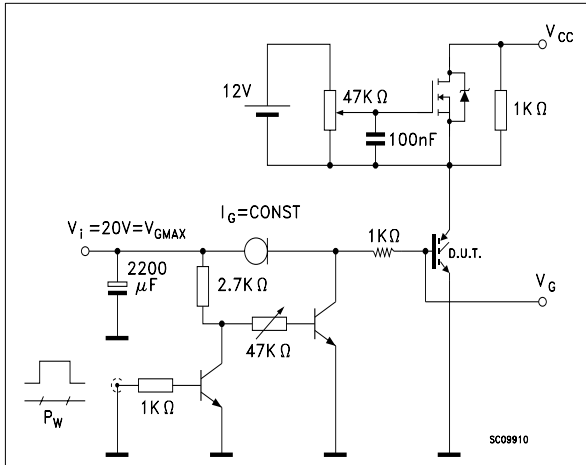
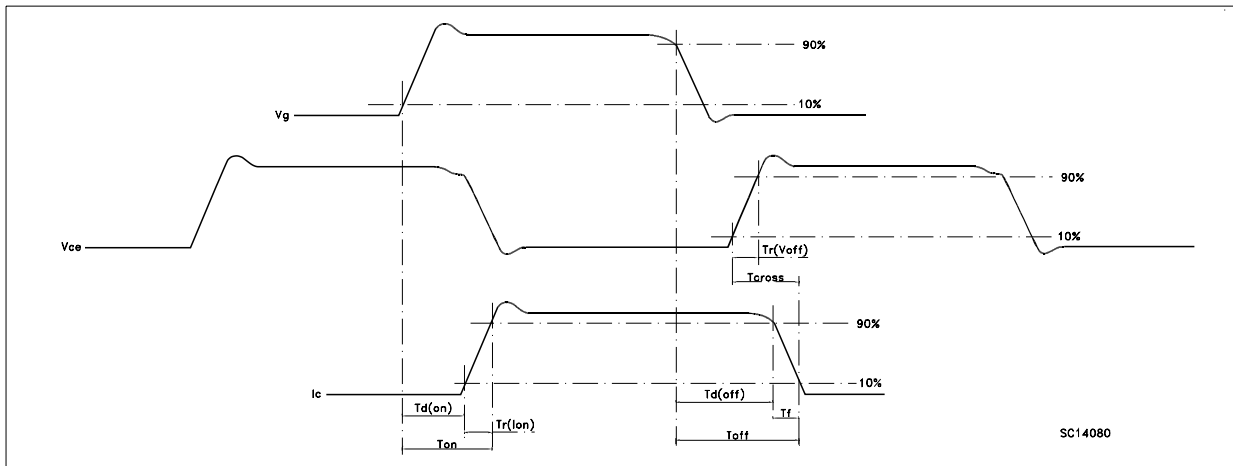
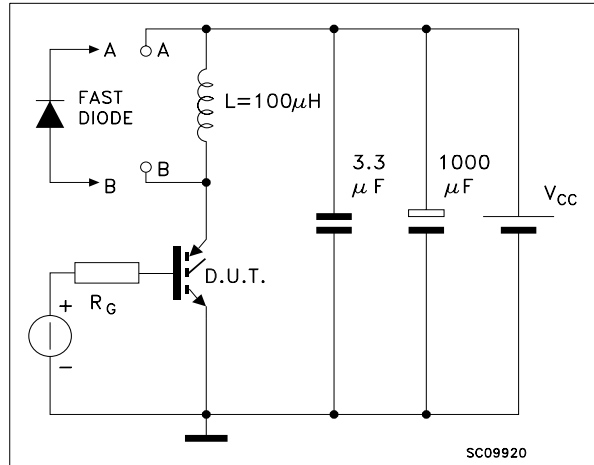
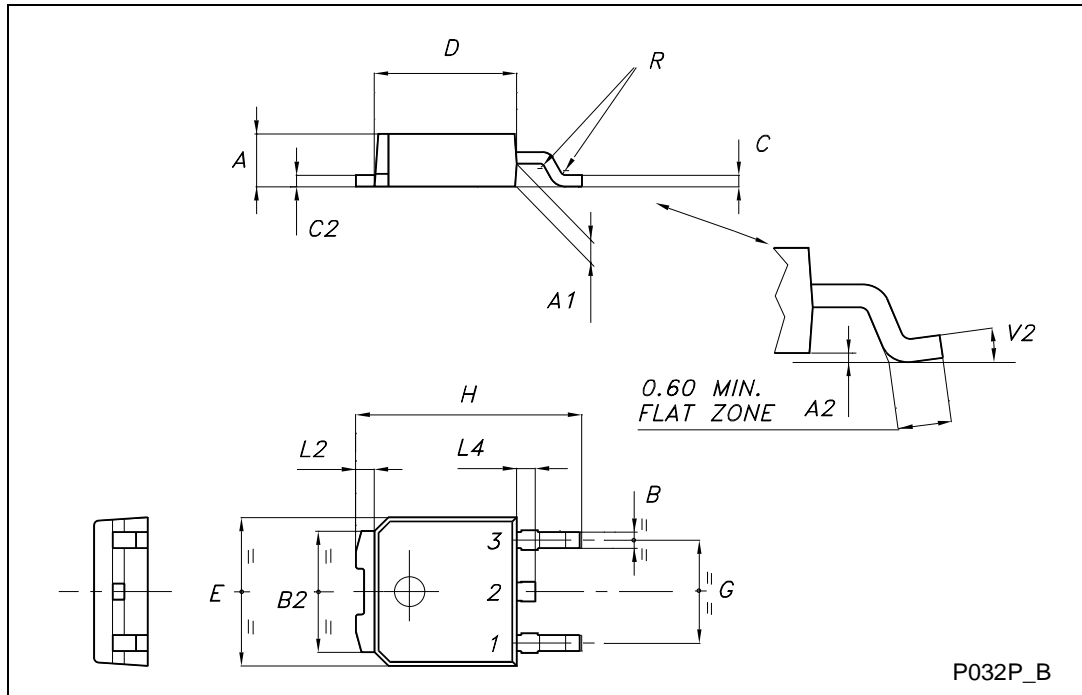


Fig. 2: Test Circuit For Inductive Load Switching



TO-252 (DPAK) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	2.20		2.40	0.087		0.094
A1	0.90		1.10	0.035		0.043
A2	0.03		0.23	0.001		0.009
B	0.64		0.90	0.025		0.035
B2	5.20		5.40	0.204		0.213
C	0.45		0.60	0.018		0.024
C2	0.48		0.60	0.019		0.024
D	6.00		6.20	0.236		0.244
E	6.40		6.60	0.252		0.260
G	4.40		4.60	0.173		0.181
H	9.35		10.10	0.368		0.398
L2		0.8			0.031	
L4	0.60		1.00	0.024		0.039
V2	0°		8°	0°		0°



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